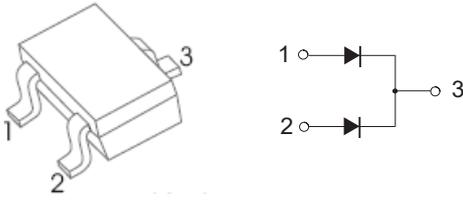
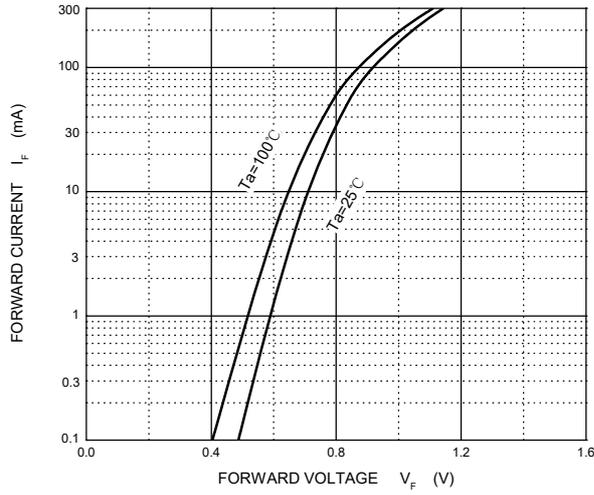


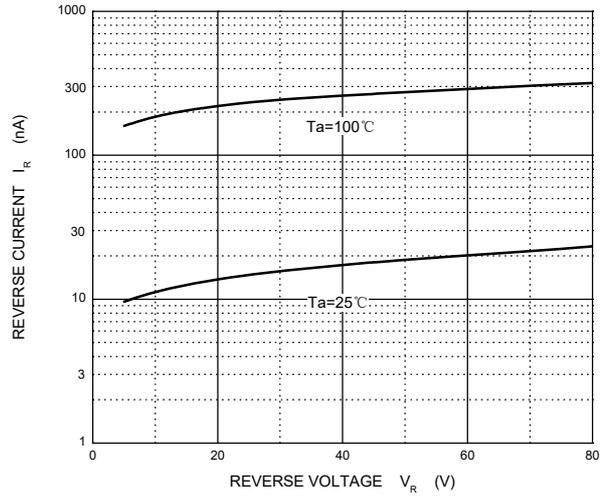
SWITCHING DIODE		SOT-323 Plastic-Encapsulate Diodes				
<p style="text-align: center;"><u>SOT-323</u></p>  <p style="text-align: center;">Marking :A4</p>		<p>Features</p> <ul style="list-style-type: none"> • Fast Switching Speed • For General Purpose Switching Applications • High Conductance 				
Maximum Ratings @Ta=25°C						
Parameter	Symbol	Limit			Unit	
Non-Repetitive Peak Reverse Voltage	V_{RM}	100			V	
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75			V	
Working Peak Reverse Voltage	V_{RWM}					
DC Blocking Voltage	V_R					
RMS Reverse Voltage	$V_{R(RMS)}$	53			V	
Forward Continuous Current	I_{FM}	300			mA	
Average Rectified Output Current	I_O	150			mA	
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0			A	
Power Dissipation	P_d	200			mW	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625			°C/W	
Junction Temperature	T_j	150			°C	
Storage Temperature	T_{STG}	-55~+150			°C	
Electrical Ratings @Ta=25°C						
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	75			V	$I_R=100\mu A$
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_{R1}			2.5	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance between terminals	C_T			2	pF	$V_R=0V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1X I_R, R_L=100\Omega$

Typical Characteristics

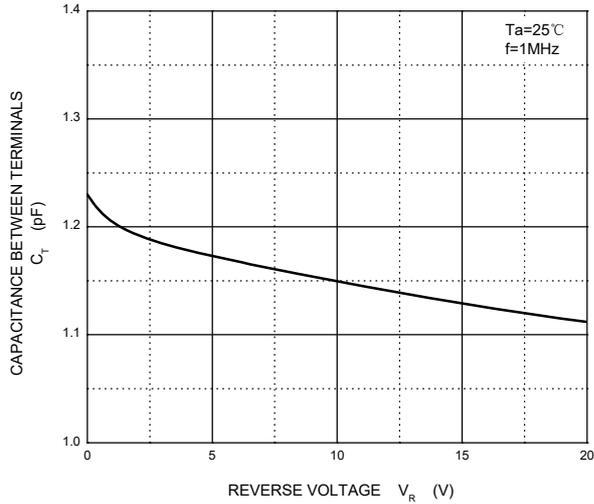
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

